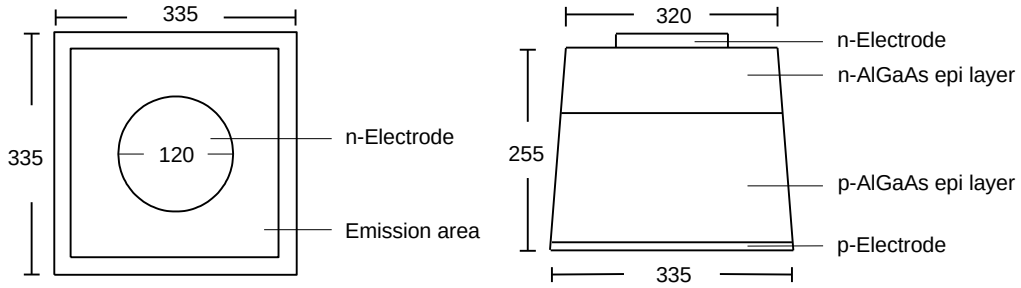
Features :

- N Side Up

Typical Applications :

- Industrial Infrared Equipment

Outline Dimensions : (Unit: um)



Physical Structure :

Chip dimension	Chip size	335 um x 335 um
	Thickness	255 um
	Emission area	320 um
	Bonding pad	120 um
Electrode	Top: N (cathode)	Gold (Aluminum optional)
	Backside: P (anode)	Gold alloy
Surface condition	Smooth	

Electro-Optical Characteristics : (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 20 mA	-	1.36	1.60	V
		I_F = 100 mA	-	1.75	2.0	
Reverse Voltage	V_R	I_R = 10 uA	5	-	-	V
Wavelength	λ_p	I_F = 20 mA	870	890	910	nm
Spectral width at half height	$\triangle\lambda$	I_F = 20 mA	-	70	-	nm
Radiant Power	P_o	I_F = 20 mA	0.40	-	-	mW

Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

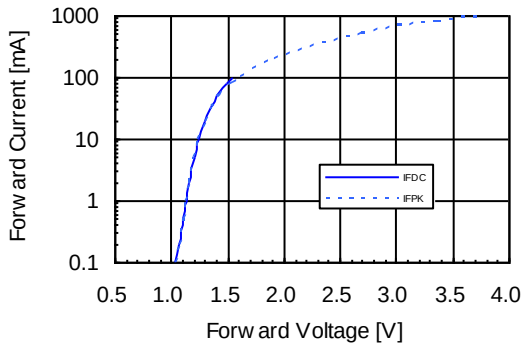


Fig 2. Relative Radiant Power vs. Wavelength

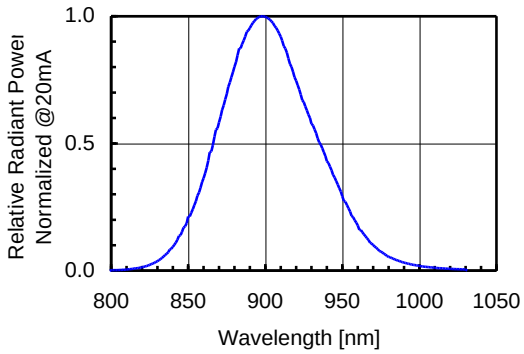


Fig 3. Relative Radiant Power vs. Forward DC Current

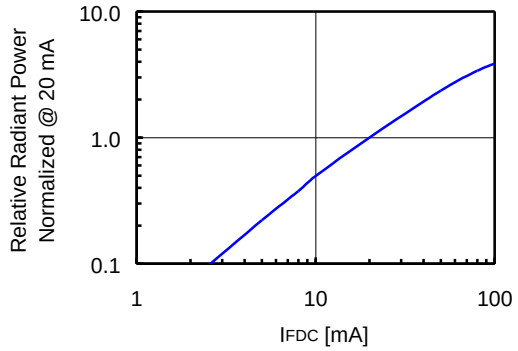


Fig 4. Relative Radiant Power vs. Forward Peak Current

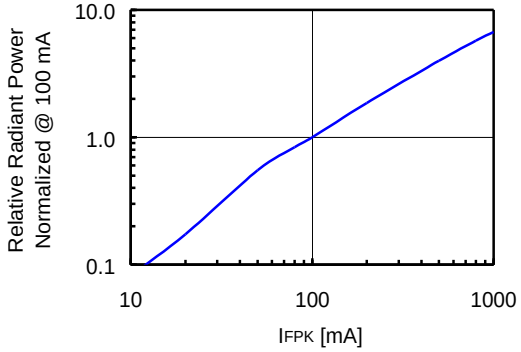


Fig 5. Forward DC Voltage vs. Temperature

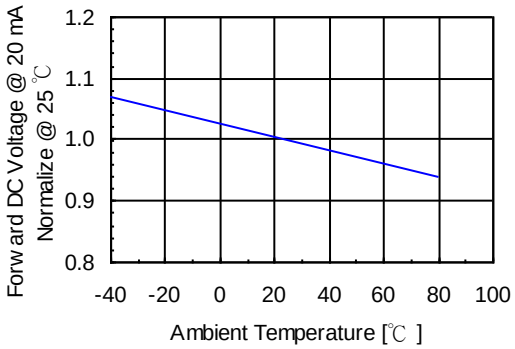


Fig 6. Relative Radiant Power vs. Temperature